A Product Line of
Diodes Incorporated

ZXMS6006SG

60V N-CHANNEL SELF PROTECTED ENHANCEMENT MODE *INTELLIFET* ® MOSFET

Product Summary

- Continuos drain source voltage 60V
- On-state resistance 100mΩ
- Nominal load current (V_{IN} = 5V) 2.8A
- Clamping Energy 480mJ

Description and Applications

The ZXMS6006SG is a self protected low side MOSFET with logic level input. It integrates over-temperature, over-current, over-voltage (active clamp) and ESD protected logic level functionality. The ZXMS6006SG is ideal as a general purpose switch driven from 3.3V or 5V microcontrollers in harsh environments where standard MOSFETs are not rugged enough.

- Lamp Driver
- Motor Driver
- Relay Driver
- Solenoid Driver

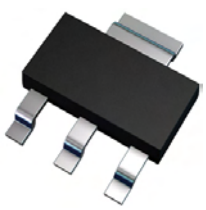
Features and Benefits

- Compact high power dissipation package
- Low input current
- Logic Level Input (3.3V and 5V)
- Short circuit protection with auto restart
- Over voltage protection (active clamp)
- Thermal shutdown with auto restart
- Over-current protection
- Input Protection (ESD)
- High continuous current rating
- **Green, RoHS Compliant (Note 1)**
- **Halogen and Antimony Free. (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

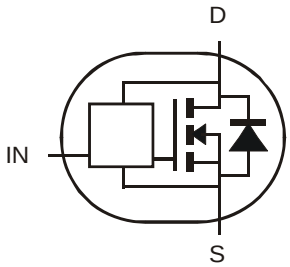
Mechanical Data

- Case: SOT-223
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish
- Weight: 0.112 grams (approximate)

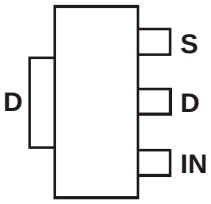
SOT-223



Top View



Device symbol



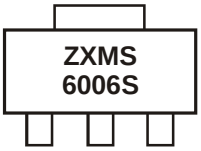
Top view
Pin Out

Ordering Information (Note 3)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXMS6006SGTA	ZXMS6006S	7	12	1,000

Notes:
1. Contain <900ppm bromine, chlorine (<1500ppm total) and <1000ppm antimony compounds.
2. Diodes Inc's "Green" Policy can be found on our website at http://www.diodes.com
3. For packaging details, go to our website at http://www.diodes.com

Marking Information



ZXMS6006S = Product type Marking Code

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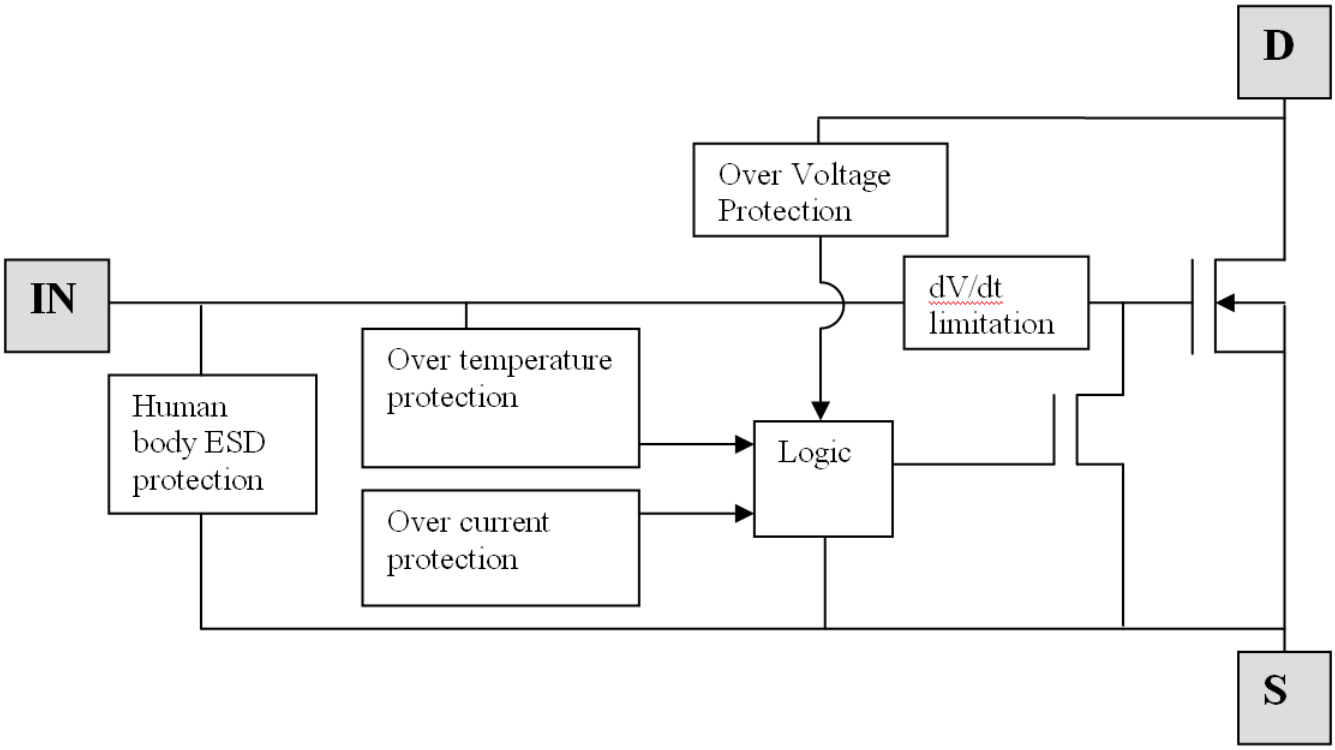
Functional Block Diagram



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Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Continuous Drain-Source Voltage	V_{DS}	60	V
Drain-Source Voltage for short circuit protection	$V_{DS(SC)}$	16	V
Continuous Input Voltage	V_{IN}	-0.5 ... +6	V
Continuous Input Current @-0.2V ≤ V_{IN} ≤ 6V Continuous Input Current @V_{IN} < -0.2V or V_{IN} > 6V	I_{IN}	No limit $\lvert I_{IN} \rvert \leq 2$	mA
Pulsed Drain Current @V_{IN} = 3.3V	I_{DM}	11	A
Pulsed Drain Current @V_{IN} = 5V	I_{DM}	13	A
Continuous Source Current (Body Diode) (Note 4)	I_S	2	A
Pulsed Source Current (Body Diode)	I_{SM}	12	A
Unclamped Single Pulse Inductive Energy, T_J = 25°C, I_D = 0.5A, V_{DD} = 24V	E_{AS}	480	mJ
Electrostatic Discharge (Human Body Model)	V_{ESD}	4000	V
Charged Device Model	V_{CDM}	1000	V

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Power Dissipation at T_A = 25°C (Note 4) Linear Derating Factor	P_D	1.0 8.0	W mW/°C
Power Dissipation at T_A = 25°C (Note 5) Linear Derating Factor	P_D	1.6 12.8	W mW/°C
Thermal Resistance, Junction to Ambient (Note 4)	$R_{\theta JA}$	125	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	83	°C/W
Thermal Resistance, Junction to Case (Note 6)	$R_{\theta JC}$	39	°C/W
Operating Temperature Range	T_J	-40 to +150	°C
Storage Temperature Range	T_{STG}	-55 to +150	°C

Notes:
4. For a device surface mounted on 15mm x 15mm single sided 1oz weight copper on 1.6mm FR4 board, in still air conditions. Sink split drain 80% and source 20% to isolate connections.
5. For a device surface mounted on 50mm x 50mm single sided 2oz weight copper on 1.6mm FR4 board, in still air conditions. Sink split drain 80% and source 20% to isolate connections.
6. Thermal resistance between junction and the mounting surfaces of drain and source pins.

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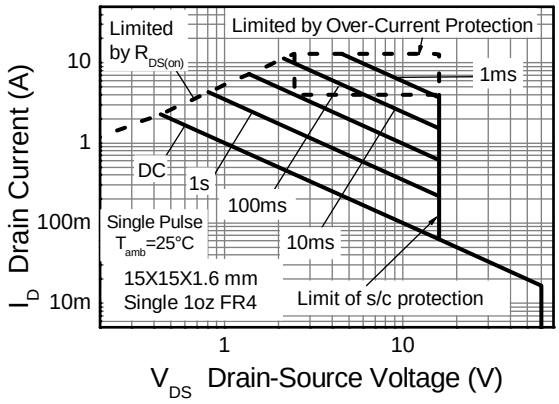
Recommended Operating Conditions

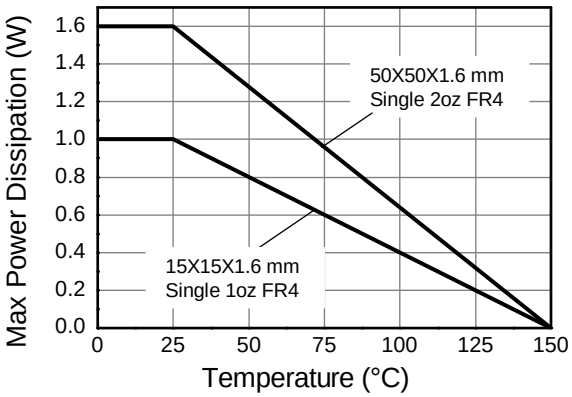
The ZXMS6006SG is optimized for use with µC operating from 3.3V and 5V supplies.

Characteristic	Symbol	Min	Max	Unit
Input voltage range	V_{IN}	0	5.5	V
Ambient temperature range	T_A	-40	125	°C
High Level Input Voltage for MOSFET to be on	V_{IH}	3	5.5	V
Low Level Input Voltage for MOSFET to be off	V_{IL}	0	0.7	V
Peripheral Supply Voltage (voltage to which load is referred)	V_P	0	16	V

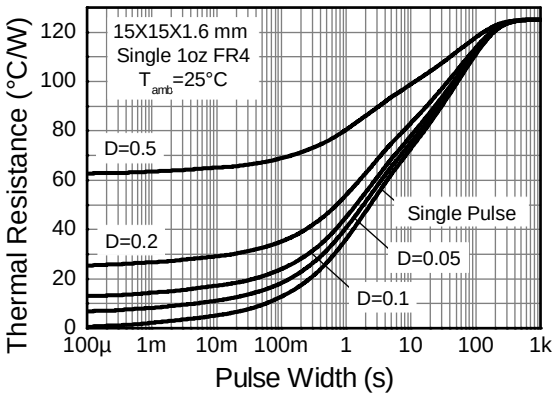
Thermal Characteristics



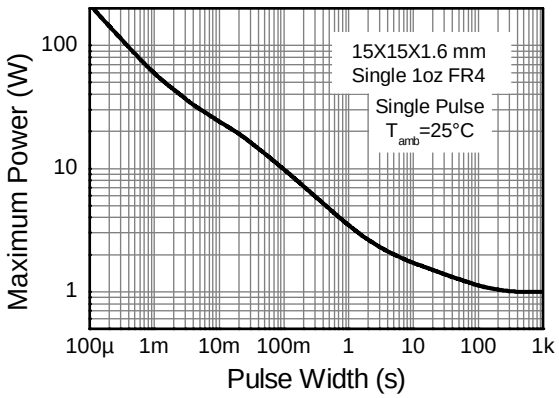
Safe Operating Area



Derating Curve



Transient Thermal Impedance



Pulse Power Dissipation

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Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Static Characteristics						
Drain-Source Clamp Voltage	$V_{DS(AZ)}$	60	65	70	V	I_D = 10mA
Off State Drain Current	I_{DSS}	-	-	1	µA	V_{DS} = 12V, V_{IN} = 0V
		-	-	2		V_{DS} = 36V, V_{IN} = 0V
Input Threshold Voltage	$V_{IN(th)}$	0.7	1	1.5	V	V_{DS} = V_{GS}, I_D = 1mA
Input Current	I_{IN}	-	60	100	µA	V_{IN} = +3V
		-	120	400		V_{IN} = +5V
Input Current While Over Temperature Active	-	-	-	300	µA	V_{IN} = +5V
Static Drain-Source On-State Resistance	$R_{DS(on)}$	-	85	125	mΩ	V_{IN} = +3V, I_D = 1A
		-	75	100		V_{IN} = +5V, I_D = 1A
Continuous Drain Current (Note 4)	I_D	2.0	-	-	A	V_{IN} = 3V; T_A = 25°C
		2.2	-	-		V_{IN} = 5V; T_A = 25°C
Continuous Drain Current (Note 5)		2.6	-	-		V_{IN} = 3V; T_A = 25°C
		2.8	-	-		V_{IN} = 5V; T_A = 25°C
Current Limit (Note 7)	$I_{D(LIM)}$	4	8	-	A	V_{IN} = +3V
		6	13	-		V_{IN} = +5V
Dynamic Characteristics						
Turn On Delay Time	$t_{d(on)}$	-	8.6	-	µs	V_{DD} = 12V, I_D = 1A, V_{GS} = 5V
Rise Time	t_r	-	18	-		
Turn Off Delay Time	$t_{d(off)}$	-	34	-		
Fall Time	f_f	-	15	-		
Over-Temperature Protection						
Thermal Overload Trip Temperature (Note 8)	T_{JT}	150	175	-	°C	-
Thermal Hysteresis (Note 8)	f_f	-	10	-	°C	-

Notes: 7. The drain current is restricted only when the device is in saturation (see graph 'typical output characteristic'). This allows the device to be used in the fully on state without interference from the current limit. The device is fully protected at all drain currents, as the low power dissipation generated outside saturation makes current limit unnecessary.

8. Over-temperature protection is designed to prevent device destruction under fault conditions. Fault conditions are considered as "outside" normal operating range, so this part is not designed to withstand over-temperature for extended periods..

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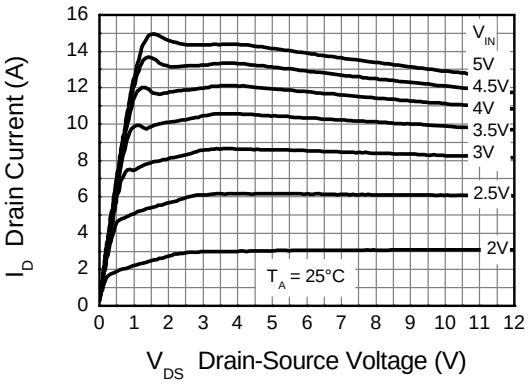
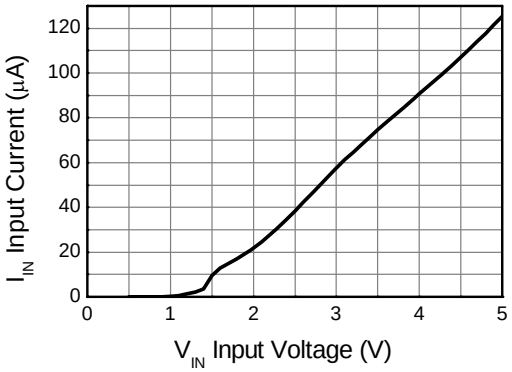
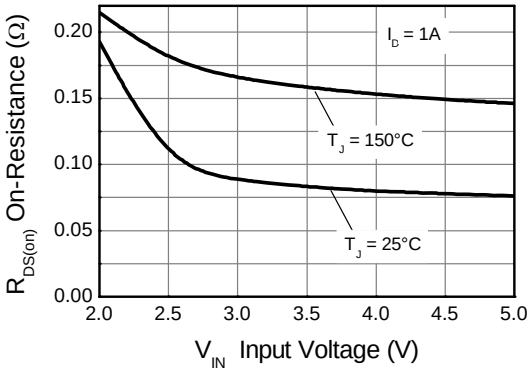
Typical Characteristics



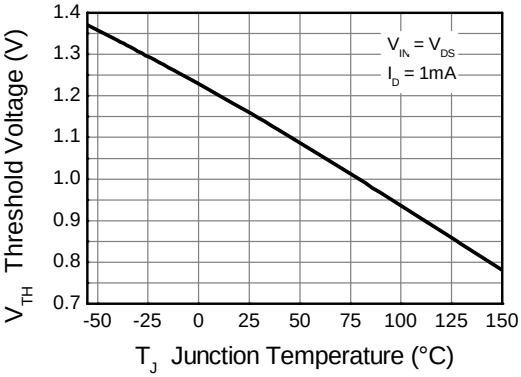
Typical Output Characteristic



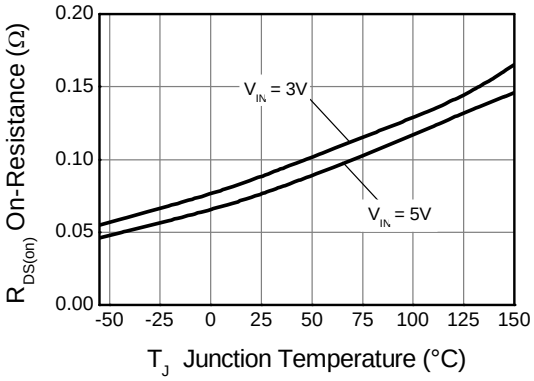
Input Current vs Input Voltage



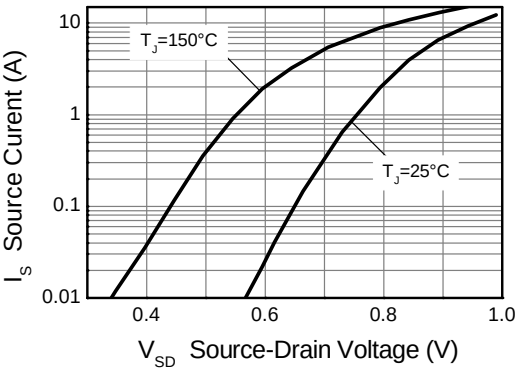
On-Resistance vs Input Voltage



Threshold Voltage vs Temperature



On-Resistance vs Temperature



Reverse Diode Characteristic

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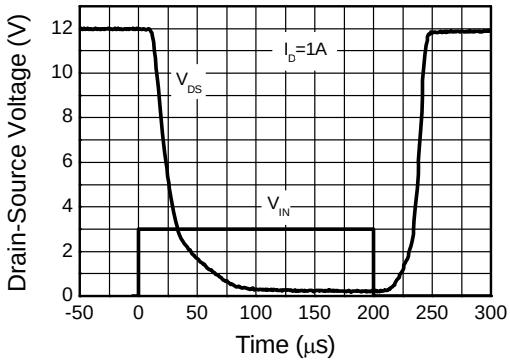
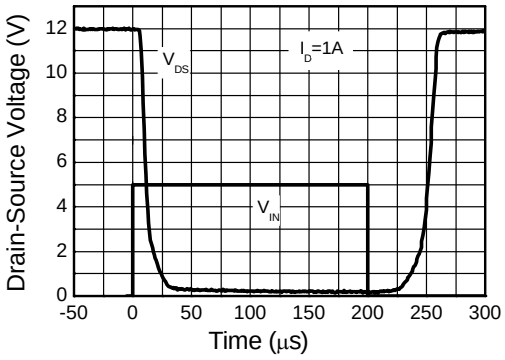
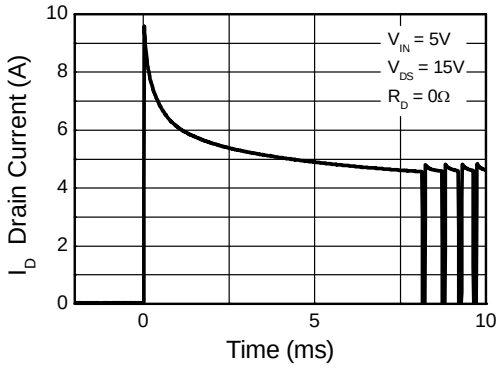
Typical Characteristics - Continued



Switching Speed



Switching Speed



Typical Short Circuit Protection

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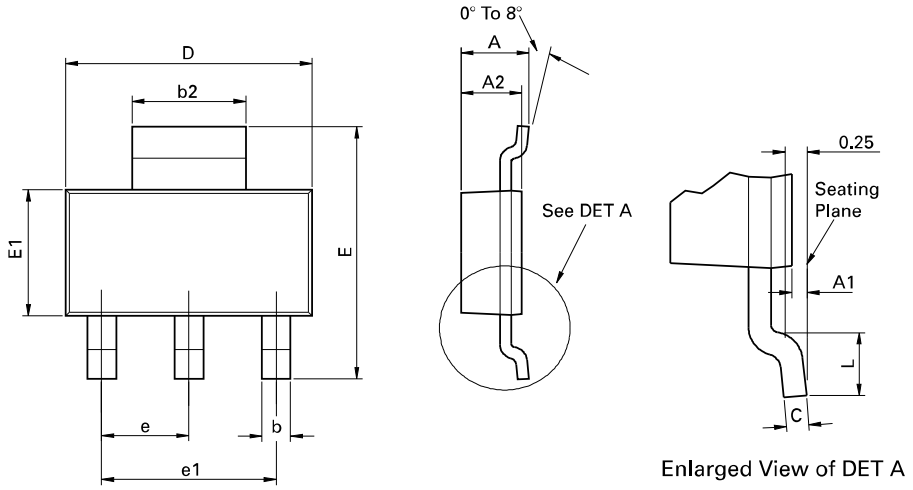
Package Outline Dimensions

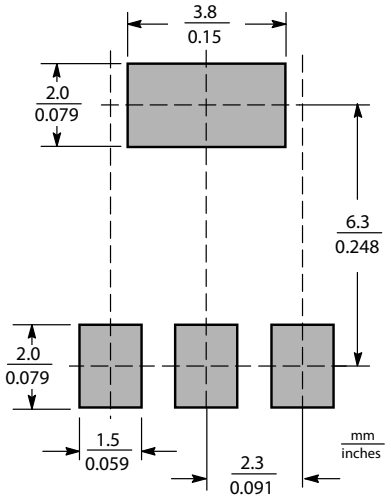


Conforms to JEDEC TO-261 AA Issue B

DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	-	1.80	-	0.071	e	2.30 BSC		0.0905 BSC	
A1	0.02	0.10	0.0008	0.004	e1	4.60 BSC		0.181 BSC	
b	0.66	0.84	0.026	0.033	E	6.70	7.30	0.264	0.287
b2	2.90	3.10	0.114	0.122	E1	3.30	3.70	0.130	0.146
C	0.23	0.33	0.009	0.013	L	0.90	-	0.355	-
D	6.30	6.70	0.248	0.264	-	-	-	-	-

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches.

Suggested Pad Layout



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